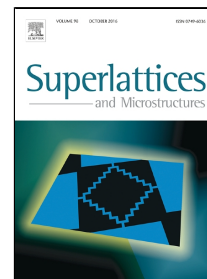


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A new low specific on-resistance Hk-LDMOS with N-poly diode

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Highlights:

A 700 V LDMOS structure using a high permittivity (Hk) dielectric is proposed.

The breakdown voltage is remarkably increased by using the Hk dielectric.

An electron accumulation layer is formed at the surface of the drift region.

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